L Number	Hits	Search Text	DB	Time stamp
_	570		USPAT	2003/06/03 14:36
_	294		USPAT	2004/08/30 16:13
_	215		USPAT	2002/07/02 13:55
	213	conductor)	OSTAT	2002/07/02 13:33
_	111	·	USPAT	2002/01/24 17:17
		conductor)	001111	2002,01,21 1,.1,
_	72	i e	USPAT;	2002/07/12 16:15
_	12	(resistor adj film)	US-PGPUB;	2002/07/12 10:15
		(resistor adj film)		
			EPO; JPO;	
			DERWENT;	
	200	057/576	IBM_TDB	0000 (07 (03 00 00
_	320		USPAT;	2002/07/03 09:20
		conductor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	İ
		000/000	IBM_TDB	0000/07/00 00 04
_	12	,	USPAT;	2002/07/03 09:34
		conductor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/05 05 ==
-	12		USPAT;	2002/07/05 08:50
		conductor)	US-PGPUB;	
			EPO; JPO;	. [
			DERWENT;	
			IBM_TDB	
-	12	1, , ,	USPAT;	2002/07/03 11:28
	·	conductor)	US-PGPUB;	
	i		EPO; JPO;	
			DERWENT;	
Ì			IBM_TDB	
-	63		USPAT;	2002/07/03 14:53
		conductor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2000/07/00 07 54
-	72	438/381 and resistor and conductor	USPAT;	2002/07/08 07:54
			US-PGPUB;	
	ì		EPO; JPO;	
			DERWENT;	
		0.57/4	IBM_TDB	0000/06/00 16 06
-	226	,, , ,	USPAT;	2003/06/03 16:36
		conduct\$3) and substrate and (wiring or	US-PGPUB;	
		terminal)	EPO; JPO;	
1			DERWENT;	
	1200	257/536	IBM_TDB	2003/10/30 15:50
_	1382	257/536	USPAT;	2003/10/30 13:50
			US-PGPUB; EPO; JPO;	
			DERWENT;	
	1201	257/536 and mariates	IBM TDB	2002/10/20 16:00
-	1321	257/536 and resist\$5	USPAT;	2003/10/30 16:06
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	40	257/536 and mariates	IBM_TDB	2004/05/12 11:01
1	42	257/536 and resist\$5 and wiring and	USPAT;	2004/05/12 11:01
		substrate and (silicon adj oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		257/526 and market /	IBM_TDB	2002/10/20 16 00
-	22		USPAT;	2003/10/30 16:29
		conduct\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L	<u> </u>		IBM TDB	

-	21	257/536 and resist\$4 and (heat adj	USPAT;	2004/05/12 10:58
		conduct\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	19	257/537 and resist\$5 and wiring and	USPAT;	2004/05/12 11:11
		substrate and (silicon adj oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	46	257/536 and resist\$5 and wiring and	USPAT;	2004/05/12 11:11
		substrate and (silicon adj oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	39	257/538 and resist\$5 and wiring and	USPAT;	2004/05/12 11:32
		substrate and (silicon adj oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	779		USPAT	2004/08/30 16:21
-	367	,	USPAT	2004/08/30 16:24
-	398	1 ' '	USPAT	2004/08/30 16:28
_	290		USPAT	2004/08/30 16:31
-	38	257/540	USPAT	2004/08/30 16:32
_	73	257/541	USPAT	2004/08/30 16:33
-	67	257/542	USPAT	2004/08/30 16:34
_	80	257/543	USPAT	2004/08/30 16:36
-	4 68	257/358	USPAT	2004/08/30 16:40
_	290		USPAT	2004/08/30 16:43
-	233		USPAT	2004/08/30 16:46
-	391	257/363	USPAT	2004/08/30 16:50
-	911	257/379	USPAT	2004/08/30 16:58
_	408	257/380	USPAT	2004/08/30 17:02
-	414	438/382	USPAT	2004/08/30 17:07
_	580	438/309	USPAT	2004/08/30 17:07